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August 2010

# FSEZ2007 — Low-Power Green-Mode EZ-PSR without Secondary Feedback (CC)

#### **Features**

- Linearly Decreasing PWM Frequency
- Green Mode Under Light-Load and Zero-Load Conditions
- Constant Current (CC) without Secondary-Feedback Circuitry
- Low Startup Current: 8µA
- Low Operating Current: 3.6mA
- Leading-Edge Blanking (LEB)
- Constant Power Limit
- Universal AC Input Range
- Synchronized Slope Compensation
- 140°C OTP Sensor with Hysteresis
- V<sub>DD</sub> Over-Voltage Protection (Auto Restart)
- Cycle-by-Cycle Current Limiting
- Under-Voltage Lockout (UVLO)
- Fixed PWM Frequency with Hopping
- Gate Output Maximum Voltage Clamped at 17V

#### **Applications**

General-purpose switching-mode power supplies and flyback power converters, such as:

- Battery Chargers for Cellular Phones, Cordless Phones, PDAs, Digital Cameras, Power Tools
- Power Adapters for Ink Jet Printers, Video Game Consoles, Portable Audio Players
- Open-Frame SMPS for TV/DVD Standby and Auxiliary Supplies, Home Appliances, Consumer Electronics
- Replacement for Linear Transformers and RCC SMPS
- PC 5V Standby Power

#### **Description**

This highly integrated PWM controller provides several features to enhance the performance of low-power flyback converters. To minimize standby power consumption, a proprietary green-mode function provides off-time modulation to linearly decrease the switching frequency under light-load and zero-load conditions. This green mode enables the power supply to meet international power conservation requirements. Another advantage is the typical startup current of only 8µA, while the typical operating current can be as low as 3.6mA. A large startup resistance can be used to achieve even higher power conversion efficiency.

FSEZ2007 integrates a frequency hopping function internally to reduce EMI emissions with minimum line filters. Built-in synchronized slope compensation maintains the stability of peak current-mode control. Proprietary internal compensation ensures constant output power limiting over a universal range of AC input voltages, from  $90V_{AC}$  to  $264V_{AC}$ .

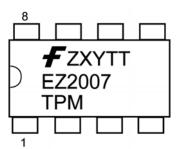
The FSEZ2007 provides many protection functions. Pulse-by-pulse current limiting ensures constant output current, even if a short circuit occurs. The internal protection circuit disables PWM output if  $V_{DD}$  exceeds 24.5V. The gate output is clamped at 17V to protect the power MOS from over-voltage damage. The built-in over-temperature protection (OTP) function shuts down the controller at 140°C with a 30°C hysteresis.

#### **Ordering Information**

Part Number	Operating Temperature Range	Package	Packing Method	
FSEZ2007NY	-40°C to +105°C	8-Lead, Dual Outline Package (DIP-8)	Tube	

#### **Application Diagram** $C_{SN2}$ R<sub>SN2</sub> V<sub>o</sub> Bridge rectifier C<sub>SN1</sub> L<sub>F1</sub> diode $D_R$ $C_{DL1} \stackrel{\rightarrow}{\sim}$ $C_{O2}$ CDL2 C<sub>01</sub> Fluse $L_{F2}$ AC line ത്ത $D_{DD}$ $R_{VDD}$ **R**<sub>Bias</sub> $N_A$ **FSEZ2007** $\gtrsim_{R_{F^1}}$ DRAIN 1 GND RFR $C_{FR}$ SOURCE 2 TL431 3 VDD 4 FB 5 $R_{F2}$ $C_{FB}$ Figure 1. Typical Application **Internal Block Diagram** DRAIN 6,7,8 OTP SENSE OVP ā osc s Internal VDD 3 OCP Vlimit ramp Blanking 2 SOURCE Circuit UVLO **PWM** Green 13V/8V 4 FB Mode Controller **≱**2R Figure 2. Functional Block Diagram

## **Marking Information**



F - Fairchild Logo

Z - Plant Code

X – 1-Digit Year Code

Y – 1-Digit Week Code

TT – 2-Digit Die-Run Code

T – Package Type (N: DIP)

P – Y: Green Package

M - Manufacturer Flow Code

Figure 3. Top Mark

## **Pin Configuration**

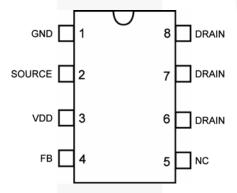


Figure 4. Pin Assignments

#### **Pin Definitions**

Pin#	Name	Description
1	GND	Ground
2	SOURCE	High-voltage power MOSFET source
3	VDD	Power supply
4	FB	The feedback (FB) pin provides feedback information to the internal PWM comparator that is used to control the duty cycle. When no feedback is provided, the pin is left open.
5	NC	No connection
6,7,8	DRAIN	High-voltage power MOSFET drain

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
$V_{VDD}$	DC Supply Voltage <sup>(1,2)</sup>		30	V
$V_{FB}$	Input Voltage to FB Pin	-0.3	7.0	V
V <sub>SENSE</sub>	Input Voltage to Sense Pin	-0.3	7.0	V
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> =25°C)		1.2	W
heta JA	Thermal Resistance (Junction to Air)		80	°C/W
TJ	Operating Junction Temperature	-40	150	°C
T <sub>STG</sub>	Storage Temperature Range	-55	150	°C
TL	Lead Temperature (Wave Soldering or IR, 10 Seconds)		260	°C
ESD	Electrostatic Discharge Capability, All Pins Except HV Pin Human Body Model (JEDEC:JESD22_A114)		2	10/
ESD	Electrostatic Discharge Capability, All Pins Except HV Pin Charged Device Model (JEDEC:JESD22_C101)		1	KV

#### Notes:

- 1. All voltage values, except differential voltages, are given with respect to the GND pin.
- 2. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.

#### **Electrical Characteristics**

Unless otherwise noted,  $V_{DD}$ =15V and  $T_A$ =25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>DD</sub> Section					•	
$V_{\text{DD-OP}}$	Continuously Operation Voltage				23.5	V
$V_{\text{DD-ON}}$	Turn-On Threshold Voltage		12	13	14	V
$V_{DD-OFF}$	Turn-Off Threshold Voltage		7.5	8.0	8.5	٧
I <sub>DD-ST</sub>	Startup Current	$V_{DD}=V_{DD-ON}-0.1V$		8	20	μA
I <sub>DD-OP</sub>	Operating Supply Current	C <sub>L</sub> =1nF		3.6	4.6	mA
V <sub>DD-G OFF</sub>	V <sub>DD</sub> Low-Threshold Voltage to Exit Green-off Mode			V <sub>DD-OFF</sub> +1.25		V
$V_{\text{DD-OVP}}$	V <sub>DD</sub> Over-Voltage Protection		23.5	24.5	25.5	٧
t <sub>D-VDDOVP</sub>	V <sub>DD</sub> Over-Voltage Protection Debounce Time		70	135	200	μs
Feedback In	put Section					
A <sub>V</sub>	Input-Voltage to Current-Sense Attenuation			0.35		V/V
$Z_{FB}$	Input Impedance	I <sub>FB</sub> =0.1mA to 0.2mA		4.6		kΩ
$V_{FB-OPEN}$	Open-Loop Voltage		4.5			٧
Current-Sen	se Section					
t <sub>PD</sub>	Propagation Delay			100	150	ns
		V <sub>DD</sub> =18V		0.81		V
V <sub>STHVA</sub>	Current Limit Valley Threshold Voltage	V <sub>DD</sub> =15V		0.73		V
		V <sub>DD</sub> =10V		0.58		V
V <sub>STHFL</sub>		V <sub>DD</sub> =18V		1.10		V
	Current Limit Flat Threshold Voltage	V <sub>DD</sub> =15V		1.01		V
		V <sub>DD</sub> =10V		0.81		V
t <sub>LEB</sub>	Leading-Edge Blanking Time		260	330	400	ns

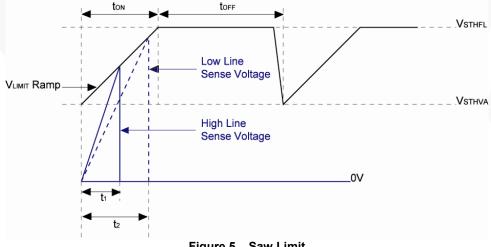


Figure 5. Saw Limit

## **Electrical Characteristics** (Continued)

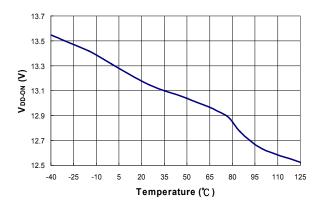
Unless otherwise noted,  $V_{DD}$ =15V and  $T_A$ =25°C.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Units
Oscillator Se	ection		1				1
fosc	_	Center Frequency		60	65	70	kHz
	Frequency	Hopping Range		±4.0	±4.6	±5.2	
t <sub>HOP</sub>	Hopping Perio	od			4		ms
f <sub>OSC-G</sub>	Green Mode	Frequency			17.0		KHz
$V_{FB-N}$	Green Mode	Entry FB Voltage			2.6		V
$V_{FB-G}$	Green Mode	Ending FB Voltage			V <sub>FB-N</sub> -0.75		V
$V_{FB-Z}$	Zero Duty Cy	cle FB Voltage			1.35		V
S <sub>G</sub>	Green Mode	Modulation Slope		40	70	100	Hz/mV
$f_{DV}$	Frequency Va	ariation vs. V <sub>DD</sub> Deviation	V <sub>DD</sub> =10 to 22V			5	%
f <sub>DT</sub>	Frequency Va Deviation	ariation vs. Temperature	T <sub>A</sub> =-20 to 85°C		1.5	5.0	%
Internal MOS	SFET Section <sup>(</sup>	3)					
$DCY_{MAX}$	Maximum Duty Cycle			70	75	80	%
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	700			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temperature Coefficient		I <sub>D</sub> =250μA, Referenced to 25°C		0.53		V/°C
Is	Maximum Continuous Drain-Source Diode Forward Current					0.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current					3.5	Α
R <sub>DS(ON)</sub>	Static Drain-S	Source On-Resistance <sup>(4)</sup>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =10V		17	19	Ω
	Drain-Source Leakage Current		V <sub>DS</sub> =700V,T <sub>C</sub> =25°C			10	μA
I <sub>DSS</sub>	Dialii-Source	Leakage Current	V <sub>DS</sub> =560V,T <sub>C</sub> =100°C			100	μA
t <sub>D-ON</sub>	Turn-On Dela	y Time	V <sub>DS</sub> =350V, I <sub>D</sub> =1A,		10	30	ns
t <sub>D-OFF</sub>	Turn-Off Delay Time		R <sub>G</sub> =25Ω		20	50	ns
C <sub>ISS</sub>	Input Capacitance		$V_{GS}$ =0V, $V_{DS}$ =25V, $f_S$ =1MHz		125	150	pF
Coss	Output Capacitance				15	18	pF
Over Tempe	rature Protect	ion (OTP)					
T <sub>OTP</sub>	Protection Ju	nction Temperature			140		°C
T <sub>OTP-RESTART</sub>	Restart Junct	ion Temperature			110		°C

#### Notes:

- 3. These parameters, although guaranteed, are not 100% tested in production.
- 4. Pulse test: pulse width ≤ 300µs, duty ≤ 2%.

## **Typical Characteristics**



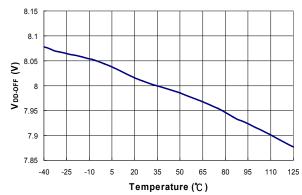


Figure 6. V<sub>DD-ON</sub> vs. Temperature

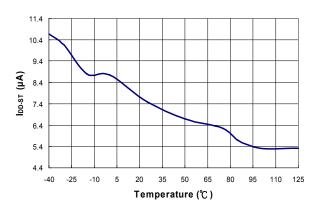


Figure 7. V<sub>DD-OFF</sub> vs. Temperature

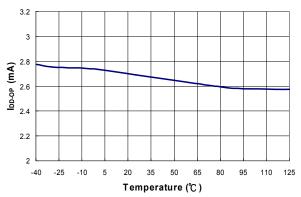


Figure 8. I<sub>DD-ST</sub> vs. Temperature

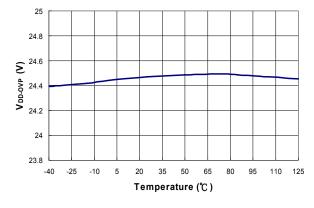


Figure 9. I<sub>DD-OP</sub> vs. Temperature

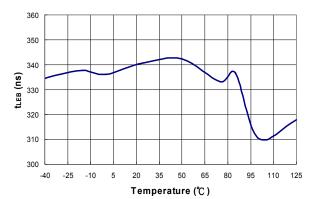
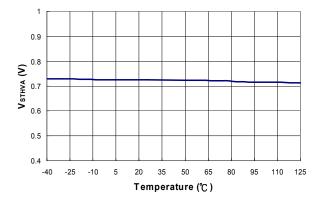


Figure 10. V<sub>DD-OVP</sub> vs. Temperature

Figure 11.t<sub>LEB</sub> vs. Temperature

## **Typical Characteristics**



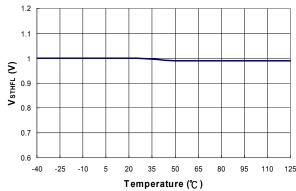
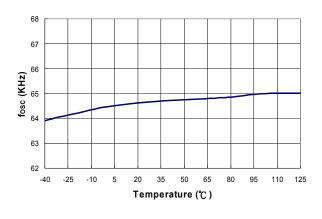


Figure 12.V<sub>STHVA</sub> vs. Temperature





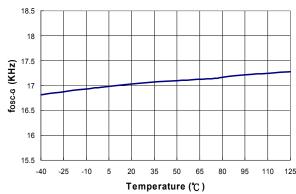
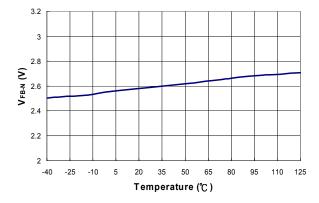


Figure 14.fosc vs. Temperature

Figure 15.f<sub>OSC-G</sub> vs. Temperature



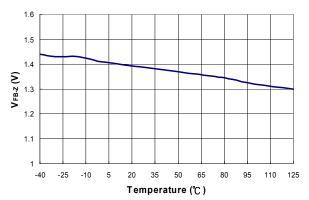


Figure 16. V<sub>FB-N</sub> vs. Temperature

Figure 17.V<sub>FB-Z</sub> vs. Temperature

#### **Operation Description**

The following highlights the FSEZ2007's key features.

#### **Startup Current**

The required startup current is only  $8\mu A$ . This allows a high-resistance, low-wattage startup resistor to supply the controller's startup power. A  $1.5 M\Omega$  / 0.25 W startup resistor can be used over a wide input range (90V- $264 V_{AC}$ ) with very little power loss.

#### **Operating Current**

The operating current is normally 3.6mA, which results in higher efficiency and reduces the required  $V_{DD}$  hold-up capacitance. A  $10\mu F$  / 25V  $V_{DD}$  hold-up capacitor can be used over a wide input range (90V-264V\_AC) with very little power loss.

#### **Green-Mode Operation**

The proprietary green-mode function provides off-time modulation to linearly decrease the switching frequency under light-load and zero-load conditions. The on-time is limited to provide better protection against brownouts and other abnormal conditions. Power supplies using the FSEZ2007 can meet international restrictions regarding standby power-consumption.

#### **Current (CC) without Feedback**

The FSEZ2007 can provide over-current protection without requiring secondary-side feedback signals. For best CV and CC accuracy, the transformer leakage inductance should be reduced as much as possible.

#### **Over-Temperature Protection (OTP)**

The FSEZ2007 has a built-in temperature sensing circuit to shut down PWM output if the junction temperature exceeds 140°C. While PWM output is shut down, the  $V_{\text{DD}}$  voltage gradually drops to the UVLO voltage. Some of the internal circuits are shut down and  $V_{\text{DD}}$  gradually starts increasing again. When  $V_{\text{DD}}$  reaches 13V, all the internal circuits, including the temperature sensing circuit, operate normally. If the junction temperature is still higher than 140°C, the PWM controller shuts down immediately. This situation continues until the temperature drops below 110°C, when the PWM output is turned back on. The temperature hysteresis window for the OTP circuit is 30°C.

#### **V<sub>DD</sub> Over-Voltage Clamping**

 $V_{\text{DD}}$  over-voltage clamping prevents damage from over-voltage conditions. When  $V_{\text{DD}}$  exceeds 24.5V, PWM output is shut down. Over-voltage conditions may be caused by an open photo-coupler loop or a short circuit in the output.

#### **Oscillator Operation**

The oscillation frequency is fixed at 65KHz.

#### Leading-Edge Blanking (LEB)

Each time the power MOSFET is switched on, a turn-on spike occurs at the sense-resistor. To avoid premature termination of the switching pulse, a 330ns leading-

edge blanking time is built in. During this blanking period, the current-limit comparator is disabled and cannot switch off the gate drive. Conventional RC filtering is not necessary.

#### **Constant Output Power Limit**

When the SENSE voltage across the sense resistor Rs reaches the threshold voltage (around 1.0V), the output GATE drive is turned off following a small propagation delay, tpd. This delay introduces an additional current proportional to t<sub>PD</sub>•V<sub>IN</sub>/L<sub>P</sub>. The propagation delay is nearly constant regardless of the input line voltage V<sub>IN</sub>. Higher input line voltages result in larger additional currents. Under high input-line voltages, the output power limit is higher than under low input-line voltages. Over a wide range of AC input voltages, the variation can be significant. To compensate for this, the threshold voltage is adjusted by adding a positive ramp (V<sub>limit ramp</sub>). This ramp signal can vary from 0.73V to 1.01V and flattens out at 1.01V. A smaller threshold voltage forces the output GATE drive to terminate earlier, reducing total PWM turn-on time and making the output power equal to that of the low line input. This proprietary internal compensation ensures a constant output power limit over a wide range of AC input voltages (90V-264V<sub>AC</sub>).

#### **Under Voltage Lockout (UVLO)**

The turn-on/turn-off thresholds are fixed internally at 13V and 8V. To enable the FSEZ2007 during startup, the hold-up capacitor must first be charged to 13V through the startup resistor. The hold-up capacitor continues to supply  $V_{DD}$  before energy can be delivered from the auxiliary winding of the main transformer.  $V_{DD}$  must not drop below 8V during this startup process. This UVLO hysteresis window ensures that the hold-up capacitor can adequately supply  $V_{DD}$  during startup.

#### **Slope Compensation**

The sensed voltage across the current sense resistor is used for current-mode control and pulse-by-pulse current limiting. The built-in slope compensation improves power supply stability. Furthermore, it prevents sub-harmonic oscillations that normally would occur because of peak-current-mode control. A positively sloped, synchronized ramp is activated with every switching cycle. The slope of the ramp is:

$$\frac{0.33 \times \text{Duty}}{\text{Duty(max.)}} \tag{1}$$

#### **Noise Immunity**

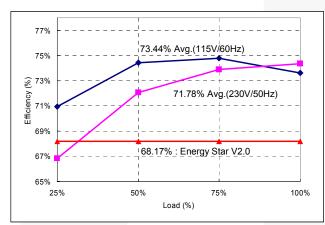
Noise from the current sense or the control signal may cause significant pulse-width jitter, particularly in continuous-conduction mode. Slope compensation helps alleviate this problem. Good placement and layout practices should be followed. Avoid long PCB traces and component leads. Compensation and filter components should be located near the FSEZ2007. Increasing the power-MOS gate resistance is advised.

## **Typical Application Circuit**

Application	Fairchild Devices	Input Voltage Range	Output
Cell Phone Charger	FSEZ2007	90~264V <sub>AC</sub>	5V/1A (5W); without cable

#### **Features**

- High efficiency (>68.17% at full load) meeting EPS regulation with enough margin
- Standby power <0.3W at no-load condition</li>
- Output regulation (CV:±0.74%, CC:±6.65%)



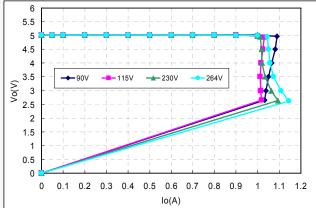


Figure 18. Measured Efficiency and Output Regulation

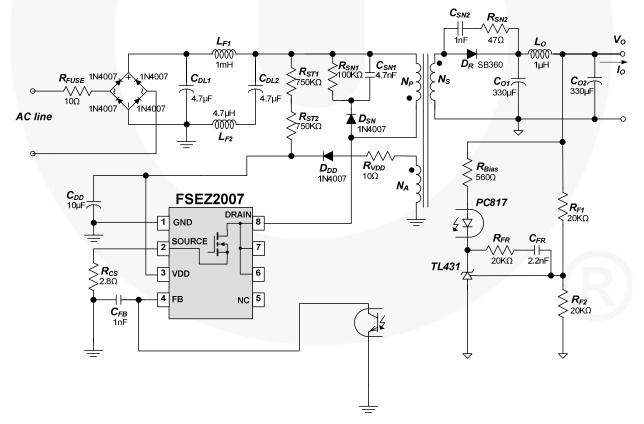


Figure 19. Schematic of Typical Application Circuit

## **Typical Application Circuit** (Continued)

## **Transformer Specification**

Core: EE16Bobbin: EE16

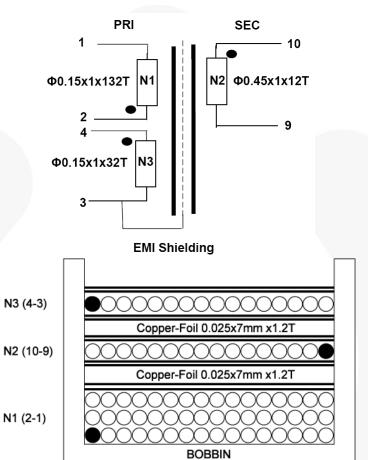


Figure 20. Transformer Diagram

	Pin	Specification	Remark
Primary-Side Inductance	1-2	2mH ± 5%	100kHz, 1V
Primary-Side Effective Leakage	1-2	40μH ± 5%	Short one of the secondary windings

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